

MILITARY SPECIFICATION
 SEMICONDUCTOR DEVICE, DIODE, SILICON,
 SWITCHING
 TYPE JAN-1N251

This amendment forms a part of Military Specification MIL-S-19500/188A, dated 9 October 1963, and is approved for use by all Departments and Agencies of the Department of Defense.

PAGE 1

1.2 Ratings, T_{op} and T_{stg} , maximum: Delete "+100" and substitute "+175".

PAGE 2

4.4.2: Delete in its entirety.

PAGE 4

TABLE II, group B inspection, subgroup 4: Delete Surge current test in its entirety and substitute the following:

"	Surge current	4066	$I_0 = 14 \text{ mAdc};$ $I_{FSM} = 200 \text{ mAdc};$ ten 1 sec. surges; 1 surge/min.	15	5	---	---	---	---	"
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TABLE II, group B inspection, subgroup 7: Delete the storage life test entirely and substitute the following:

"	High-temperature life (nonoperating)	1031	$T_A = 175^\circ\text{C}$	$n = 7$	---	---	---	---	---	"
	End points: (same as subgroup 6)									

Custodians:
 Army - ER
 Navy - EC
 Air Force - 17

Review activities:
 Army - MI, AR
 Air Force - 11, 19, 99
 DLA - ES

User activities:
 Army - AV, SM
 Air Force - 13, 15
 Navy - AS, CG, MC, OS, SH

Preparing activity:
 Navy - EC

Agent:
 DLA - ES

(Project 5961-0738)